

PATENT ABSTRACTS OF JAPAN

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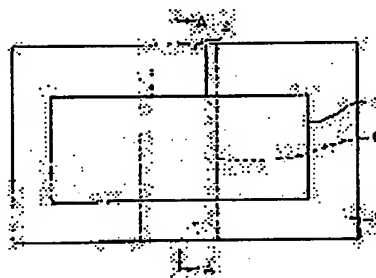
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(54) SEMICONDUCTOR DEVICE**(57)Abstract:**

PURPOSE: To prevent floating and to stabilize the characteristics of device by providing an element isolating region containing an isolating region to be connected with an insulating layer arranged below an element forming semiconductor substrate, and an insulating region not connected with the insulating layer.

CONSTITUTION: An insulating film 2 is provided on an Si substrate 1, an element forming substrate 3 is provided thereon, and a shallow isolating region 4 is provided on one side of the substrate whereas a deep isolating region reaching to the insulating film 2 is provided on the other side. An insulating film 12 is provided on the element forming substrate 3 and the isolating regions 4, 5, and a gate 6 is provided thereon. In other words, the shallow isolating region, i.e., the channel region of transistor where the gate 6 is superposed on the element forming region 7, is provided not to reach to the insulating film 2 for that channel region. The element forming substrate 3 exists below the shallow isolating region 4, and contact with substrate potential can be made from the outside of the element region 7 through the substrate 3 at that part. By such arrangement, floating can be prevented and the characteristics of device can be stabilized.

**LEGAL STATUS**

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